

16 GB DDR4 SDRAM UDIMM Specification

Specifications

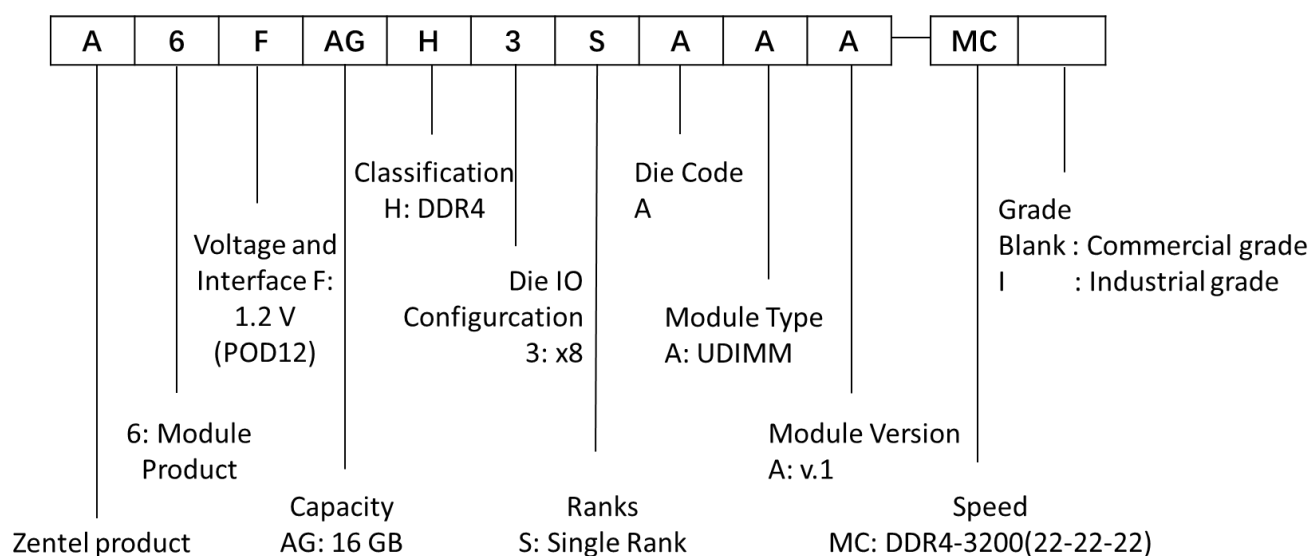
| | |
|---------------------------|-----------------|
| Max. Speed; CAS Latency | DDR4-3200@CL=22 |
| Row Cycle Time (tRCmin) | 45.75 ns |
| Row Active Time (tRASmin) | 32 ns(min.) |

Features

- 288-pin, unbuffered dual in-line memory module (UDIMM)
- 1Rx8 memory module (1 rank of x8 DDR4 SDRAMs)
- Power supply:
 - VDD = VDDQ = 1.2 V \pm 5%
 - VPP = 2.5 V $-5\%/+10\%$
 - VDDSPD = 2.2 V to 3.6 V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Low-power auto self refresh (LPASR)
- Data bus inversion (DBI) for data bus
- On-die VREFDQ generation and calibration
- On-board I²C serial presence-detect (SPD) EEPROM
- 16 internal banks; 4 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- Terminated control command and address bus
- PCB Height: 1.23" (31.25 mm)

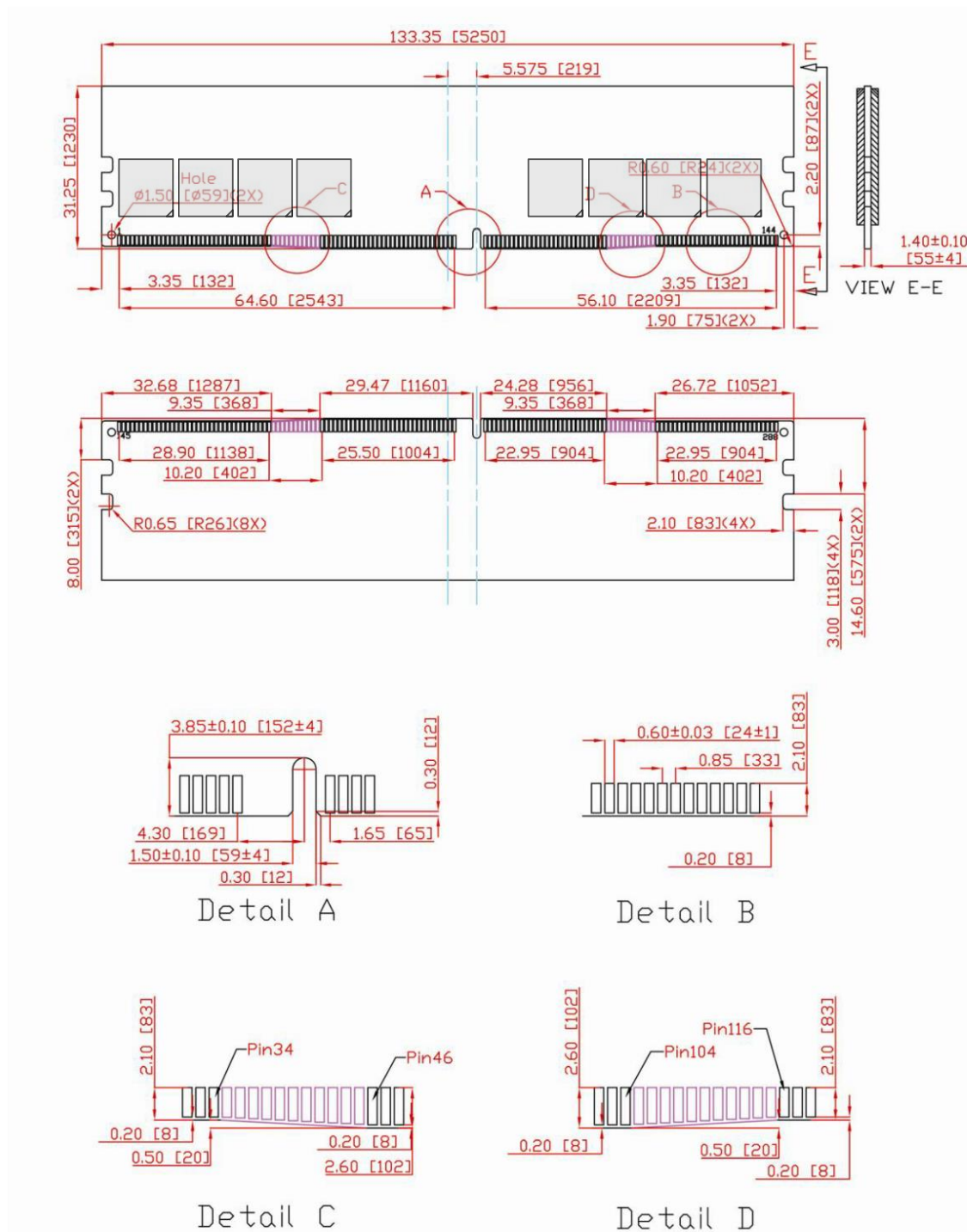
1. Ordering Information

| Part Number | Module Density | Configuration | Speed Bin (CL-nRCD-nRP) | Operating Temperature | Storage Temperature |
|-----------------|----------------|-------------------------|-------------------------|-----------------------|---------------------|
| A6FAGH3SAAA-MC | 16 GB | 2G × 64 (2Gx8 1Rank) | DDR4-3200 (22-22-22) | 0 °C to +85 °C | -55 °C to +100 °C |
| A6FAGH3SAAA-MCI | | | | -40 °C to +85 °C | -55 °C to +150 °C |



Module Dimensions

All dimensions are in millimeter[mils] and should be kept within a tolerance of +/- 0.15[6], unless otherwise specified.





| Change History | | | |
|--------------------------------------|------|------------|---|
| Document No.: DSA6FAGH3SAAAF.(Rev.#) | | | |
| Rev. # | Who | When | What |
| 01 | Rik | 2023-05-04 | Initial version derived from DSA6FAGH3SAAAZF.01; Updated header and footer |
| 02 | Abby | 2023-05-10 | Updated Ordering Information |